Silicon-on-Insulator Technology and Devices 13

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Table of Contents

Preface iii

Session 1
Technology, Process Integration, Radiation Hardness

Embedding Device Solutions in Engineered Substrates ***** 3
C. Mazure

Physics and Integration of Fully-Depleted Silicon-On-Insulator Devices ****** 15
A. Vandooren

Impact of Metal Silicide Layout Covering Source/Drain Diffusions on Parasitic Resistance of Triple-Gate SOI MOSFET 27
K. Yoshimoto, Y. Omura and H. Wakabayashi

High dose Implantation Impact on the Carrier Mobility in Ultra-Thin Unstrained and Strained SOI Films 33
C. Dupre, P. Fazzini, T. Ernst, F. Cristiano, J. Hartmann, A. Claverie, F. Andrieu, O. Faynot, P. Rivallin, F. Laugier, G. Ghibaudo, S. Cristoloveanu and S. Deleonibus

Low Temperature Chatacterization of High-k Dielectric Metal Gate FD-SOI nMOSFETs 39
L. Zafari, J. Jomaah, G. Ghibaudo, O. Faynot and A. Vandooren

Uniaxial Strain Enhancement in SOI Technology for the Improvement of Channel and Exterior Resistances 45
D. Zhang, D. Goedeke, V. Dhandapani, J. Hildreth, C. Fu, T. Kropewnicki, A. Lu, M. Jahanbani, H. Martinez, R. Noble, D. Eades, N. Liu, L. Kang, B. Nguyen, V. Kolagunta, M. Hall, J. Cheek and S. Venkatesan

Heavy Ion Induced Upset Cross-Sections of 150nm SOI CMOS SRAMs Fabricated in UNIBOND 51
M. S. Liu, D. K. Nelson, J. C. Tsang and H. L. Hughes

Session 2
FinFETS and other Devices

Intrinsic Advantages of SOI Multiple-Gate MOSFET (MuGFET) for Low Power Applications ** 59
W. W. Xiong, C. Cleavelin, C. Hsu, M. Ma, K. Schruefer, K. Von Arnim, T. Schulz, I. Cayrefourcq, C. Mazure, P. Patruno, M. Kennard, K. Shin, S. Xin, T. King Liu, K. Cherkaoui and J. Colinge

Fabrication and Power-Management Demonstration of Four-Terminal FinFETs ** 71
K. Endo, Y. Liu, M. Masahara, T. Matsukawa, S. O'uchi and E. Suzuki

Parasitic Effects Depending on Shape of Spacer Region on FinFETs 83
Y. Kobayashi, K. Tsutsui, K. Kakushima, V. Hariharan, V. Rao, P. Ahmet and H. Iwai

Modelling the Back-Gate Coupling effect in Triple-, Π- and Ω-Gate FETs 89
R. Ritzenthaler, M. Gaillardin, K. Akarvardar, O. Faynot, C. Jahan and S. Cristoloveanu

Origin of Transient Gate Current Observed in Pseudo-MOS Transistor 95
S. Sato, T. Nguyen, S. Cristoloveanu and Y. Omura

Impact of Improved Mobilities and Suppressed 1/f Noise in Fully Depleted SOI MOSFETs Fabricated on Si(110) Surface 101
W. Cheng, A. Teramoto, C. Tye, P. Gaubert, M. Hirayama, S. Sugawa and T. Ohmi

The "C" Shape Behavior of the Floating Body Effect in Function of Temperature in PD SOI nMOSFETs 107
P. G. Agopian, J. A. Martino, E. Simoen and C. Claeys

Hot Carrier Instability Mechanism in Accumulation-Mode Normally-off SOI nMOSFETs and Their Reliability Advantage 113
R. Kuroda, A. Teramoto, W. Cheng, S. Sugawa and T. Ohmi

Session 3
TFTs, Photons, Phonons, and Electrons

Thin Film Transistor and ULSIC Technologies - Parallel or Crossing? *** 121
Y. Kuo

Integration of SOI-Based 2D- and Si-Based 3D Photonic Crystals **	133
G. Kocher, W. Khunsin, J. Romero Vivas, K. Vynck, S. Arpiainen, S. Romanov, B. Langer, M. Mulot, F. Jonsson, T. Charvolin, E. Hajdi, D. Cassagne, R. Zentel, J. Ahopelto and C. M. Sotomayor Torres

Complementary Single-Crystal Silicon TFTs on Plastic	139
H. Yuan, Z. Ma, C. Ritz, D. Savage, M. Lagally and G. Celler

Instability of Threshold Voltage of Flexible Single-Crystal Si TFTs	145
H. Pang, H. Yuan, M. Lagally, G. Celler and Z. Ma

Heat Generation and Transport in SOI and GOI Devices **	151
E. Pop

Electronic and Thermal Properties of Silicon Nanowires	159
E. B. Ramayya, D. Vasileska, S. Goodnick and I. Knezevic

Analysis of PD SOI pMOSFET Device Performance Enhancement due to Direct-Tunneling Current in the Partial n+ Poly Gate	165
G. Guegan, J. Pretet, R. Gwoziecki, O. Gonnard, G. Gouget, P. Touret, C. Raynaud and S. Deleonibus

Session 4
Poster Papers

Non-Contact Photoelectric Method For Thin SOI Characterization	173
E. Tsidilkovski and K. Steeples

Implant Metrology for Bonded SOI Wafers using a Surface Photo-Voltage Technique	179
A. F. Bertuch, W. Smith, K. Steeples, R. Standley, A. Stefanescu and R. Johnson

Low Temperature Properties of Multi-Independent-Gate FET (MIGFET) Operating in Single-Gate and Double-Gate Modes	185
K. Na, S. Eminente, S. Cristoloveanu, L. Mathew, A. Vandooren, Y. Bae and J. Lee

Analysis of Trench Gate Power LDMOS Transistors in Thin SOI Technology	191
I. Cortes, P. Fernández-Martinez, D. Flores, S. Hidalgo and J. Rebollo

Assessment of the CBR Quantum Transport Simulator on Experimentally Fabricated Nano-FinFET	197
H. Khan, D. Mamaluy and D. Vasileska

Simple Analytical Model to Study the ZTC Bias Point in FinFETs 205
M. Bellodi, L. Camillo, J. A. Martino, E. Simoen and C. Claeys

Temperature Influences on FinFETs with Undoped Body 211
M. A. Pavanello, J. A. Martino, E. Simoen, R. Rooyackers, N. Collaert and C. Claeys

Application of Double Gate Graded-Channel SOI in MOSFET-C Balanced Structures 217
R. T. Doria, M. A. Pavanello, A. Cerdeira, J. Raskin and D. Flandre

Session 5
Material Characterization

SOI Metrology and Characterization in Modern Wafer Production ****** 225
O. Kononchuk, F. Brunier and M. Kennard

Investigation of Apertureless NSOM for Measurement of Stress in Strained Silicon ****** 235
C. McDonough, J. Atesang, Y. Wang and R. Geer

Effective Control of Strain in SOI by SiN Deposition 245
D. Kosemura, A. Ogura, K. Yamasaki, Y. Kakemura and T. Yoshida

Structural Properties of Tensile-Strained Si Layers Grown on $Si_{1-x}Ge_x$ Virtual Substrates (x = 0.2, 0.3, 0.4 and 0.5) 251
J. Hartmann, D. Rouchon, J. Barnes, M. Mermoux and T. Billon

X-ray Absorption Spectroscopy of Strained-Si Nanomembranes 257
C. Euaruksakul, Z. Li, D. Savage and M. Lagally

Comparison of Different Etching Techniques in Order to Reveal Dislocations in Thick Ge Layers 263
A. Abbadie, J. Hartmann, C. Deguet, L. Sanchez, F. Brunier and F. Letertre

A Chromium-free Defect Etching Solution for Application on SOI 271
J. Maehliss, A. Abbadie and B. Kolbesen

Mobility Characterization by Magnetoresistance in Ultra Thin SOI Ring-FETs 279
T. V. Chandrasekhar Rao, S. Cristoloveanu, J. Antoszewski, T. Nguyen, H. Hovel, P. Gentil and L. Faraone

Session 6
Technology and Materials

Strained Silicon Directly on Insulator (SSOI): Biaxial, Uniaxial, or Hybrid Strain? ** 287
A. Thean

Mixed Orientation Si-Si Interfaces by Hydrophilic Bonding and High Temperature Oxide Dissolution: Wafer Fabrication Technique and Device Applications ** 295
K. Saenger, J. de Souza, K. Fogel, J. Ott, A. Reznicek, H. Yin, C. Sung and D. Sadana

Fabrication of SOI MOSFET by "Separation by Bonding Silicon Islands (SBSI)" Method 309
K. Kanemoto, H. Oka, H. Hisamatsu, Y. Matsuzawa, Y. Kitano, T. Hara, M. Hoshina, S. Ohmi and J. Kato

Epitaxial Regrowth of Ge on SGOI and GeOI Substrates Obtained by Ge Condensation 315
J. Damlencourt, Y. Campidelli, M. Roure, B. Vincent, E. Martinez, F. Fillot, B. Arrazat, T. Nguyen, S. Cristoloveanu, L. Clavelier and Y. Morand

Ordered Lattices of Quantum Dots on Ultrathin SOI Nanomembranes 321
C. Ritz, F. Flack, D. Savage, D. Detert, P. Evans, M. Lagally and Z. Cai

LEGO Process for Mixed Power Applications: Fabrication at Low Cost of Localized Thick SOI Layers 327
I. Bertrand, J. R. Dilhac, P. Renaud, M. Bafleur and C. Ganibal

A Novel Method to Fabricate Multiple-layer SOI -- Single-Crystal Si Nanomembrane Transfer and Stacking 333
W. Peng, M. Roberts, E. Nordberg, F. Flack, P. Colavita, R. Hamers, D. Savage, M. Lagally and M. Eriksson

Strained Silicon-On-Insulator - Fabrication and Characterization 339
M. Reiche, C. Himcinschi, U. Gösele, S. Christiansen, S. Mantl, D. Buca, Q. Zhao, S. Feste, R. Loo, D. Nguyen, W. Buchholtz, A. Wei, M. Horstmann, D. Feijoo and P. Storck

Advanced Heterostructure Si-InSb on Insulator Formed by Bonding of Hydrogen Transferred Si Layer and Implanted SiO2 Film 345
V. P. Popov, I. Tyschenko, E. Cherkov, G. P. Pokhil, V. M. Fridman and M. Voelskow

Session 7
Computer Simulations

Atomic-Scale Simulations of Electron Mobilities in Ultrathin SOI MOSFETs ** 353
S. T. Pantelides, G. Hadjisavvas, M. Evans, L. Tsetseris, M. Caussanel and R. Schrimpf

A Comprehensive Study of the Corner Effects in Pi-Gate SOI MOSFETs 363
F. G. Ruiz, A. Godoy, F. Gamiz, C. Sampedro and L. Donetti

Impact of Phonon-Limited Mobility Superiority in Double-Gate or Fin FET with a (111) Si and (001) Ge Surface Channel on Device Scaling 369
T. Yamamura, S. Sato and Y. Omura

Significance of Gate Underlap Architecture in FinFETs for Low-Voltage Analog/RF Applications 375
A. Kranti and G. Armstrong

Non-Vertical Sidewall Angle Influence on Triple-Gate FinFETs Corner Effects 381
R. Giacomini and J. A. Martino

Improved Model to Determine the Generation Lifetime in Short Channel SOI nMOSFETs 387
M. Galeti, J. A. Martino, E. Simoen and C. Claeys

Author Index 393

***** *Plenary paper*
****** *Invited paper*
******* *Electronics and Photonics Division Award Address*